

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	251	"6011725"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:40
L2	2	"6011725".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:42
L3	98	"5966603"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:42
L4	0	"5966603".clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:43
L5	2	"5966603".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:43
L6	84	((silicon adj nitride) or (siN)) near10 (program or programming or programmed) near10 charge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:44
L7	6	((silicon adj nitride) or (siN)) near10 (program or programming or programmed) near10 charge). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:48
L8	17	((silicon adj nitride) or (siN)) near10 (program or programming or programmed) near10 charge near10 (inject or injecting or injected or injection))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:49
L9	4	((silicon adj nitride) or (siN)) near10 (program or programming or programmed) near10 charge near10 (inject or injecting or injected or injection) near10 (perform or performing or performed))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:50

L10	4	((silicon adj nitride) or (siN)) with (program or programming or programmed) near10 charge near10 (inject or injecting or injected or injection) near10 (perform or performing or performed))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:50
L11	4	((silicon adj nitride) or (siN)) with (program or programming or programmed) with charge near10 (inject or injecting or injected or injection) near10 (perform or performing or performed))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:50
L12	4	((silicon adj nitride) or (siN)) with (program or programming or programmed) with charge with (inject or injecting or injected or injection) near10 (perform or performing or performed))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:50
L13	5	((silicon adj nitride) or (siN)) with (program or programming or programmed) with charge with (inject or injecting or injected or injection) with (perform or performing or performed))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:51
L14	32	((silicon adj nitride) or (siN)) with (program or programming or programmed) with charge with (inject or injecting or injected or injection))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:51
L15	2	((silicon adj nitride) or (siN)) with (program or programming or programmed) with charge with (inject or injecting or injected or injection)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:52
L16	32	((silicon adj nitride) or (siN)) with (program or programming or programmed) with charge with (inject or injecting or injected or injection))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:53
L17	10	((silicon adj nitride) or (siN)) with (program or programming or programmed) with charge with (inject or injecting or injected or injection) with channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:55
L18	1	((silicon adj nitride) or (siN)) with (program or programming or programmed) with charge with (inject or injecting or injected or injection) with channel).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:55

L19	2	(((silicon adj nitride) or (SiN)) with (program or programming or programmed) with charge with (inject or injecting or injected or injection) with channel) and (semiconductor adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:56
L20	3	(((silicon adj nitride) or (SiN)) with (program or programming or programmed) with charge with (inject or injecting or injected or injection) with channel).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:56
L21	36	(US-20030229981-\$ or US-20030230143-\$ or US-20040104425-\$ or US-20040224534-\$ or US-20040266109-\$ or US-20040119122-\$ or US-20040179396-\$ or US-20050093057-\$ or US-20040070026-\$ or US-20030155607-\$ or US-20030151950-\$ or US-20030142550-\$ or US-20040095808-\$ or US-20020179958-\$ or US-20050045943-\$).did. or (US-6829937-\$ or US-6862795-\$ or US-6011725-\$ or US-5966603-\$ or US-5104819-\$ or US-6849905-\$ or US-6894344-\$ or US-6862220-\$ or US-6785165-\$ or US-6744670-\$ or US-6674122-\$ or US-6531735-\$ or US-6788583-\$ or US-6774432-\$).did. or (JP-2004179387-\$).did. or (US-20040104425-\$ or US-6011725-\$ or US-5966603-\$ or JP-2004221554-\$ or US-20030178652-\$ or US-20030103383-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/06/23 20:56
L22	8	I21 and (semiconductor adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 20:57
L24	20	((silicon adj nitride) or SiN) near dot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 21:06

L25	1018	((silicon adj nitride) or SiN) near (particles or particulate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 21:06
L26	109	((silicon adj nitride) or SiN) near (particles or particulate)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 21:06
L27	0	(program or programming or programmed or programmable) with (((silicon adj nitride) or SiN) near (particles or particulate)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 21:07
L28	1	(program or programming or programmed or programmable) with (((silicon adj nitride) or SiN) near (particles or particulate or dot)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 21:07
L29	2	(program or programming or programmed or programmable) with (((silicon adj nitride) or SiN) near (particles or particulate or dot))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 21:07
L30	0	((silicon adj nitride) or SiN) near (particles or particulate or dot)) and nonvolatile	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 21:07
L31	11	((silicon adj nitride) or SiN) near (particles or particulate or dot)) and nonvolatile	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 21:07